

Title (en)

DRY ETCH STOP PROCESS FOR ELIMINATING ELECTRICAL SHORTING IN MRAM DEVICE STRUCTURES

Title (de)

TROCKENÄTZVERFAHREN ZUR BESEITIGUNG ELEKTRISCHER KURZSCHLÜSSE BEI MRAM-GERÄTESTRUKTUREN

Title (fr)

PROCEDE D'ARRET DE GRAVURE A SEC POUR ELIMINER UN COURT-CIRCUIT ELECTRIQUE DANS DES STRUCTURES DE DISPOSITIF MRAM

Publication

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Application

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Abstract (en)

[origin: WO2007109117A2] The present invention relates generally to semiconductor fabrication and particularly to fabricating magnetic tunnel junction devices. In particular, this invention relates to a method for using the dielectric layer in tunnel junctions as an etch stop layer to eliminate electrical shorting that can result from the patterning process.

IPC 8 full level

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